

## Supporting Information

### **Fabrication and electrical properties of printed three-dimensional integrated carbon nanotube PMOS inverters on flexible substrates**

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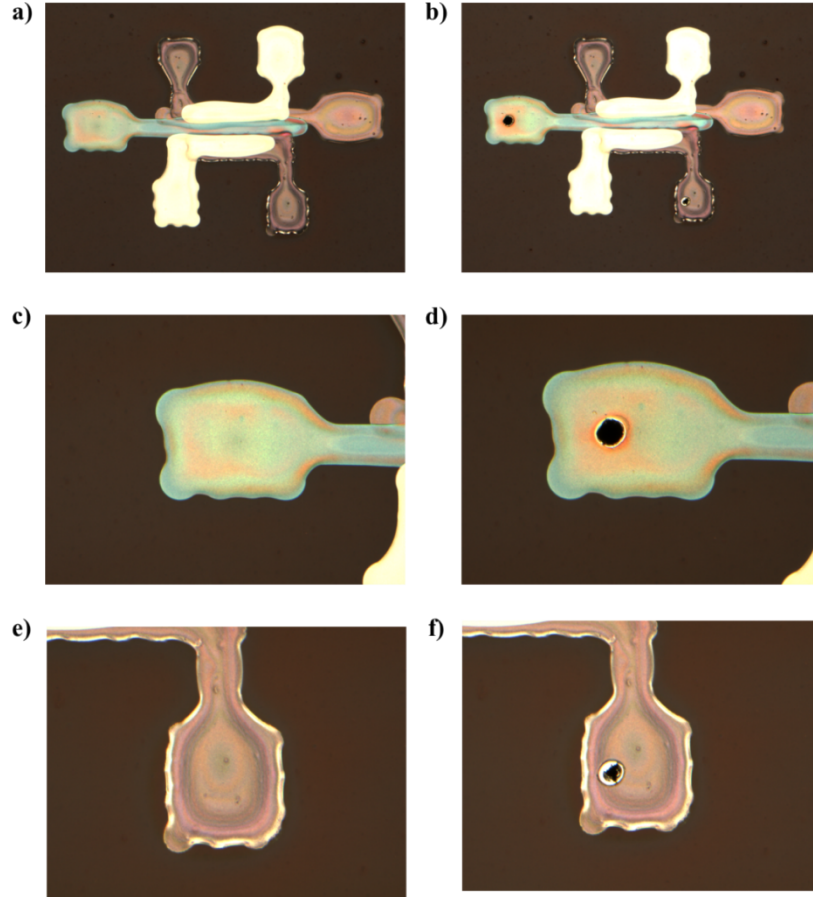
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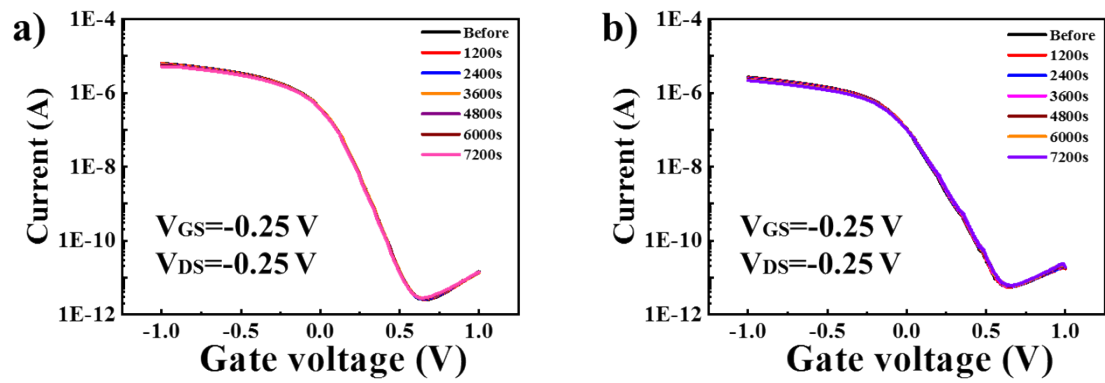
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**Figure S1:** a, b) Manufacturing positions of through-holes in the manufacturing of SWCNT 3D PMOS inverters printed on PI substrates. c-f) Through-holes prepared by laser drilling.



**Figure S2:** Transfer characteristic ( $I_{DS}$ - $V_{GS}$ ) curves of a) bottom-layer device and b) top-layer device measured every 1200 s under continuous bias ( $V_{DS} = -0.25$  V,  $V_{GS} = -0.25$  V).